# C onductance of a $Q$ uantum $P$ oint $C$ ontact in the presence of a Scanning $P$ robe M icroscope $T$ ip 

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#### Abstract

U sing the recursive $G$ reen's function technique, we study the coherent electron conductance of a quantum point contact in the presence of a scanning probe $m$ icroscope tip. Im ages of the coherent fringe inside a quantum point contact for di erent widths are obtained. It is found that the conductance of a speci c channel is reduced while other channels are not a ected as long as the tip is located at the positions correspending to that channel. M oreover, the coherent fringe is sm oothed out by increasing the tem perature or the voltage across the device. O ur results are consistent $w$ ith the experim ents reported by Topinka et al. (Science 289, 2323 (2000)).


PACS num bers: 7323.6 , 73.43.C d, 7320 At
(Phys. Rev. B 65, 205321 (2002))

Q uantum point contacts (QPCs) form ed in twodim ensional electron gases (2D EG s) have attracted signi cant attention for the past two decades ${ }^{12 n t i n}$ Since the discovery of the conductance quantization in these structures ${ }^{1 / 2}$ QPCs have been widely used in a variety of investigations, including transport through quantum dots, the quantum H all e-pct, m agnetic focusing, and the A haronov-B ohm e ect ${ }^{21}$ A lso, w th the rapid developm ent on scanning probem icroscope (SP M) techniques, it is possible to im age current directly to study $m$ apy rem arkable phenom ena, including quantum corrals, ${ }^{\mathfrak{A}}$ electron ow through nanostructures, ${ }^{4 / 4}$ charge distribution and photoactivity of, dopant atom $s_{L}^{15}$ and spectra of $m$ etallic nanoclusters' ${ }^{\prime}$ ' Since the Q PC plays such an im portant role in $m$ esoscopic devioes, it is an ideal system to be studied by the SPM techniques.

Very recently, Topinka et al. have directly im aged the electron ow from the QPC by scanning a negatively charged SPM tip above the surface of the device and $m$ easuring the position-dependent conductance
 the QPC increases, the conductance increases in quantized steps of $2 e^{2}=h$, as was also reported in other experim ents ${ }^{11}$ Besides, several new and interesting features were observed. W idening of the angular structure ofelectron ow hasbeen clearly seen as the QPC channel becom es w ider. A nother feature of their im ages is the appearance of fringes spaced by half the Ferm iw avelength transverse to the electron ow, which clearly show s the character of coherent quantum interference. The above fringes are them ally sm eared out by increasing the effective electron tem perature. M oreover, when the tip is placed such that it intermupts the ow from particular modes of the QPC, a reduction can be observed in the conductance-pf those channels, while other channels are not a ected ${ }_{2}^{1 / 1}$ On the other hand, it is also found that, in contrary to intuitions, the electron ow from the
point contact form s narrow branching strands instead of sm oothly spreading fans's'
$U$ sing the recursive $G$ reen's function technique, in this paper, we study theoretically a mesoscopic structure sim ilar to the experim ental oner results are able to explain the experim ental nding in $R$ efs.7,8. Therefore, the recursive $G$ reen's fiunction technique seem $s$ to be a suitable $m$ ethod to study the coherent electron conductance in such a $m$ esoscopic system.


Fig. 1

FIG.1. Schem atic diagram of the system .
W e consider a negatively charged SPM tip capacitively coupled to the 2 DEG where the QPC is form ed. The effect of SPM tip is that, the conductance will decrease if the tip is positioned over regions with high electron ow from the QPC, while it $w i l l$ be less modied if the tip is at low electron ow regions. The electron ow can be im aged by scanning the tip over the twodim ensional surface. Two contributions to the potential in the 2 D EG region should be taken into account. O ne is
from the negatively charged gates that de ne the QPC, which wem odelw th the Buttiker saddle-point potential $U(x ; y)=V_{g} \quad m \quad{ }_{x}^{2} x^{2}=2+m \quad!{ }_{y}^{2} y^{2}=2 w$ th $V_{g}$ as the gate voltage, $m$ as the electron e ective $m$ ass and $!_{x ; y}$ as the strength of the lateral con nem ent. T his potential is a practical candidate to reproduce the quantized conductance of a Q PC 'a ${ }^{9}$ The other is a Lorentzian type potentialinduced by the SPM tip ${ }^{10}$. which we approxim ate as a delta function in the present work: $\mathrm{V}_{\mathrm{SPM}}=\mathrm{V}_{\mathrm{t}}\left({ }_{(1)}^{\prime} \quad \dot{I}_{\mathrm{t}}\right)$, $w$ here $1_{t}$ denotes the position of the $t i p$, and $V_{t}$ is a negative constant. It is worth noting that the num erical results obtained $w$ ith the sim ple delta potential are consistent the experim ental results ${ }^{171281}$

W e use a 2D square lattioe model to describe the QPC system. The sites of the lattice are denoted as (na;m a) w ith a to be set equal to unit, $n=1 ; 2 ;:: ; \mathrm{N}$ and $m=1 ; 2 ;::: ; \mathrm{M}$. T he lattice m ay be divided into three regions, as show $n$ in $F$ ig.1. The shadow ed central zone is a m esoscopic structure w th a Buttiker saddlepoint potential and scanned by a SPM tip. B oth sides of the structure are assum ed to be connected w ith sem iin nite ideal leads to sim plify scattering boundary conditions. The one-electron-tight-binding H am iltonian of the system takes the form 111

$$
\begin{aligned}
& \mathrm{H}=\mathrm{X}^{\mathrm{X}} \quad \mathrm{n}_{\mathrm{n} ; \mathrm{m}} \text { jn; } \mathrm{m} \text { ihn;m } j \\
& \mathrm{X}_{\mathrm{X}} \text {; }
\end{aligned}
$$

$$
\begin{aligned}
& n ; m
\end{aligned}
$$

where $t=h^{2}=2 m \quad a^{2}$ and in; $m$ is a orthonorm al set in the lattice sites $(n ; m)$. T he on-site energy in the central zone is given by $"_{n ; m}=U_{n ; m}+V_{S P M}+4 t$. Then the H am iltonian for this region reads

$$
\begin{equation*}
\left.H_{c}=X_{n=1}^{X^{N}} j n\right) H_{n}\left(n j+X_{n=1}^{X_{n}^{1}}(j n) H_{n ; n+1}(n+1 j+H: C:) ;\right. \tag{2}
\end{equation*}
$$

where in) denotes the set of $M$ ket vectors belonging to the $n$-th œell, and
$\left(\mathrm{H}_{\mathrm{n} ; \mathrm{n} 1}\right)_{\mathrm{pp}^{0}}=\left(\mathrm{H}_{\mathrm{n} ; \mathrm{n}+1}\right)_{\mathrm{pp}^{0}}=\mathrm{t}_{\mathrm{pp}}{ }^{0}\left(\mathrm{p} ; \mathrm{p}^{0}=1 ;:: ; \mathrm{M}\right)$ :
The H am iltonians for the two ideal leads have the sam e form as Eq. $\bar{Z}_{1}$ ), but $w$ ith di erent sum $m$ ing regions ( $1<\mathrm{n}<1$ at the left lead and $\mathrm{N}<\mathrm{n}<1$ at the right lead) and $"_{n ; m}=4 t$.

U sing the recursive $G$ reen's function technique, the transm ission am plitude for the incident channel 1 and outgoing channel $j$ is found to be $\operatorname{l}^{1+1212}$

$$
\begin{equation*}
t_{l j}=q \overline{V_{j}=V_{l}}{ }_{k_{j}}^{+} G_{N+1 ; 0} \quad \text { (E) } \quad k_{k_{1}} \mathrm{e}^{i k_{j} L_{x}} ; \tag{3}
\end{equation*}
$$

where $v_{j}=@ E=h @ k_{j}$ with $P_{M}^{E}=4 t \quad 2 t$ (cosk $_{j}+$ $\cos j=(M+1)),(E)=2$ it $\quad{ }_{l=1}^{M} Q_{1} \operatorname{sink}_{1} w$ ith
$\left(Q_{1}\right)_{p p^{0}}=\frac{2}{M+1} \sin \frac{l p}{M+1} \sin \frac{l p^{0}}{M+1} ;\left(p ; p^{0}=1 ; \quad ; M\right):$
The set of vectors ${ }_{\mathrm{k}_{j}}^{+}$are the duals of the set ${ }_{k_{1}}$, de ned by ${ }_{k_{j}}^{+} k_{1}={ }_{j 1}$ where

$$
k_{j}=\frac{r}{\frac{2}{M+1}}\left(\sin \frac{j}{M+1} ;::: ; \sin \frac{j m}{M+1} ;::: ; \sin \frac{j M}{M+1}\right)^{T_{r}}
$$

$w$ ith $T_{r}$ as the transposition of $m$ atrix. $G_{N+1 ; 0}$ is the retarded $G$ reen's function for the scattering region betw een two ideal leads, which can be obtained by a set of recursion form ulas in a m atrix form

$$
\begin{align*}
\mathrm{G}_{\mathrm{n}^{0}+1 ; 0} & =\operatorname{tg}^{\mathrm{n}^{0}+1} \mathrm{G}_{\mathrm{n}^{0} ; 0} ;\left(\begin{array}{lll}
0 & \mathrm{n}^{0} \quad \mathrm{~N}
\end{array}\right)  \tag{4}\\
\mathrm{g}^{\mathrm{n}^{0}+1} & =\left(\begin{array}{lll}
\left(\begin{array}{l}
n^{0}+1
\end{array}\right. & \mathrm{t}^{2} g^{\mathrm{n}^{0}}
\end{array}\right)^{1} ; \tag{5}
\end{align*}
$$

by iteration starting form $g^{0}=G_{0 ; 0}=\left(\begin{array}{ll}E & \left.P_{P}\right)^{1} \text {, where }\end{array}\right.$ $\mathbb{P}_{1}=H_{1}\left(\begin{array}{lll}1 & \mathrm{~N}\end{array}\right)$, and $\mathbb{F}=H \quad t^{P} \underset{j=1}{M} e^{i k_{j}} Q_{j}$ ( $=0 ; \mathrm{N}+1$ ) .
At nite tem perature $T$, the conductance through a 2 D
(1) m esoscop,ic structure is given by the Landauer-B uttiker formulal

$$
\begin{equation*}
G(T)={\frac{2 e^{2}}{h}}_{l ; j}^{X_{1}} T_{1 j} \frac{@ f(E ; T)}{@ E} d E ; \tag{6}
\end{equation*}
$$

where $\mathrm{T}_{1 j}=\mathrm{J}_{1 j}{ }^{\rho}$ is the transm ission coe cient, and $\mathrm{f}(\mathrm{E} ; \mathrm{T})=\left[1+\exp \left(E \quad E_{F}\right)=\mathrm{k}_{\mathrm{B}} T\right]^{1}$ is the Ferm i-D irac distribution $w$ th $E_{F}$ as the Ferm i energy and $k_{B}$ as the Boltzm ann constant. O byiously, at zero tem perature Eq. (G) reduces to $G=2 e^{2}=h \quad f 1 ; j g T_{l j}$.

The above form ulas are valid under the assum ption that the voltage across the device is low. H igh voltage w ill raise the energies ofelectrons, ow ing from the Q PC. $T$ hus, as show by van $W$ ees et al. 15 the conductance at a nite voltage $V$ has a sim ilar behavior to that $w$ ith $a$ nite tem perature e ect, and is given by

$$
\begin{equation*}
G(V)=\frac{2 e}{h} \frac{1}{V}_{l ; j} X_{E_{F}}^{Z_{E}+e V} T_{l j} d E: \tag{7}
\end{equation*}
$$

In the follow ing we calculate num erically the conductance ofaQPC system with the size $\mathrm{N}=15$ and $\mathrm{M}=11$. $W$ e set $t$ and the lattice constant $a$ as the units of energy and length, respectively. In order to obtain wellpronounced quantized plateaus w ith the B uttiker saddlepoint potential, we choose $!_{\mathrm{y}}=2!_{\mathrm{x}}, \mathrm{E}_{\mathrm{F}}=2 \mathrm{t}$, and $V_{t}=1: 5 t$.


FIG.2. Im ages of electron ow across a Q PC at zero tem perature and low voltage for three di erent w idths corresponding to (a) the rst conductance plateau, $\mathrm{V}_{\mathrm{g}}=0: 7 \mathrm{E}_{\mathrm{F}}$; (b) the second plateau, $\mathrm{V}_{\mathrm{g}}=0: 4 \mathrm{E}_{\mathrm{F}}$; (c) the third plateau, $V_{g}=0 \cdot 2 \mathrm{E}_{\mathrm{F}}$. The color scale show s the change $\mathrm{G}=\mathrm{G} \quad \mathrm{G} 0$ in QPC conductance as the tip is scanned above the device.

At zero tem perature and low voltage lim it, im ages of electron ow from the 2D surface of the QPC are plotted in F ig 2. The gate voltage $\mathrm{V}_{\mathrm{g}}$ is chosen to ensure Fig 2 (a) - (c) correspond to the rst, the second and the third conductance plateau of the QPC, respectively. It is seen clearly that a new electron ow pattem appears when a higher mode is opened (then the conductance of the QPC rises to another plateau) by decreasing the gate voltage. $T$ h is feature agrees $w$ ith the result reported in Ref.7: electronic wavefunctions inside the QPC have N m axim a when QPC has N conductance modes. N ote that the im ages do not tum into sm oothly spreading fans as the electrons ow across the QPC from the left to the right. Instead, they form branching strands which are relatively narrow er. In fact, even the width of the sam ple decreases to $M=6$ in the calculation, the im ages change little (not show $n$ here). It is not supprising that strands are form ed in our m odel since the electrons are laterally con ned. On the other hand, a sim ilar but also striking phenom enon is reported in $R$ ef.8, where the strands were found in regions far aw ay from the point contact. So we can see that the electron path has a rare probability to pass through the edge regions of the sam ple, and thus the im purity density and the boundary scattering in these re-
gions are less relevant to the conducting property of the QPC.M oreover, the fringe structures due to the alternating constructive and destructive interference of electrons are evident in Fig 2, though the distribution is nat, so hom ogeneous when com pared w th the experim ents ${ }_{2}^{\eta_{1}}$ This inhom ogenetly induced from the varieties of electron wavelength inside the QPC is the m ain di erence betw een the structure of fringe inside and outside QPC. It is worth pointing out that the fringes directly dem onstrate the coherent character of electron ow in QPC.


Fig. 3

FIG.3. The conductance plateaus of the Q PC for the selective e ect of the SPM tip. T he solid line represents the curve w ithout SPM tip, and the dash line is the curve with the SPM placed over certain position such that it blocks the electron ow from (a) the rst $m$ ode, or (b) the second $m$ ode.

M eanw hile, we also note that the angular structures in these electron ow pattems are quite di erent from each other, especially for the rst and second $m$ odes. For the rst m ode, the pattem contains one branch only, while there are tw o branches for the second $m$ ode. So there are som e regions in the 2D surface where the distribution of electrons at one $m$ ode $m$ ake no contribution to the other m ode. A s reported in experim ents $r^{\prime \cdot 1}$ when the SPM tip is placed over these regions, only the ow from particular channels of the QPC are changed, while other channels are not a ected. This phenom enon is clearly $m$ anifested in Fig.3, where the quantized $G \quad V_{g}$ curves of the Q P C w th orw thout the SPM tip are plotted. From the com parison betw een the behaviors of the solid line and the
dash line in F ig. 3 (a), we can see that when the tip is placed at the central axis of the QPC where the electrons from the rstm odetravelthrough, the heights ofall plateaus are reduced. But the height di erence betw een each pair of neighboring plateaus rem ains to be $2 \mathrm{e}^{2}=\mathrm{h}$, except for that betw een the rst plateaus and the 0 -axis. In Fig. 3 (b), the SPM tip is positioned o the central axis. A ccording to $F$ ig 2 (a) and (b), we can leam that this position corresponds to $G \quad 0$ in the rst mode, and it only a ects the second mode. Thus in Fig. 3 (b) it is shown that the rst conductance plateau is alm ost unchanged, and the second and other higher plateaus are low ered. A gain, the height di erence betw een the second and the third plateaus still rem ains to be $2 e^{2}=h$.


Fig. $4(a, b, c)$


Fig.4(a', $\left.\mathrm{b}^{\prime}, \mathrm{c}^{\prime}\right)$

FIG.4. E ect of electron heating on im ages of ow. (a-c) show electron ow for the rst, second and third conductance plateaus under the voltage $\mathrm{eV}=0: 05 \mathrm{t}$. ( $\mathrm{a}^{0} \quad \mathrm{c}^{0}$ ) show corresponding im ages for higher voltage $\mathrm{eV}=0: 2 \mathrm{t}$. O ther param eters are the sam e as those in F ig 2.

The electron ow s under the nite voltages across the QPC are im aged in Fig.4, where (a c) are at a low voltage ( $\mathrm{eV}=0: 05 \mathrm{t}$ ) and ( $\mathrm{a}^{0} \quad \mathrm{c}^{0}$ ) are at a high voltage $(\mathrm{eV}=0: 2 \mathrm{t})$. C om paring it w ith F ig 2 , we see that the pattem still rem ains the sam $e$ in each $m$ ode, but the values of $G$ is no longer so severely uctuated when the voltage is raised. A m ore im portant characteristic ofvoltage e ect is that fringe structure w ould gradually disappear as the voltage rises. A ctually, we nd that the three conductance m odes gradually merge into one conductance m ode, which im plies that the quantized plateaus also disappear as the voltage is increased. The origin of the fringes is the coherent quantum interference ${ }^{\frac{1}{7}}$ Since the fringes are less perceptible as the uctuation of $G$ becom es paci ed, it is $m$ anifested that the consequence of using e ectively hotter electrons is to sm ear out the coherence am ong electrons. The above properties are sim ilar for elevating tem perature as the physicale ects of tem perature and voltage are the sam e here ${ }^{15}$. C learly, the voltage e ect addressed here is in qualitative agree$m$ ent $w$ ith the experim ental observation ?

In conclusion, we have calculated the conductance of a QPC in the presence of the SPM tip by the recursive $G$ reen's function technique. The num erical results are $a b l e$ to explain the experim ental results in $\mathrm{Refs} .7,8$.

This work was supported in part by the RGC grant of Hong K ong under G rant No. HKU7118/00P. G. P. H. was supported in part by the NSF of Guangdong Province (C ontract No.011151) and the Foundation of Zhongshan U niversity Advanced R esearch C entre (C ontract No.02P 2). Z. D. W . also thanks support in part from the Texas C enter for Superconductivity at the University of H ouston. S.L.Z.was supported in part by the $\mathrm{N} S \mathrm{SF}$ of G uangdong under G rant N O. 021088.
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